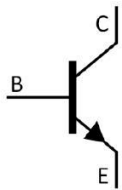


Rev.D Dec.-2015

WR0<5 M M E QSQ Æ M y s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

$\beta \geq 100$
High gain, good linearity of h_{FE} .

TV final picture IF amplifier applications.



PIN1 χ Collector

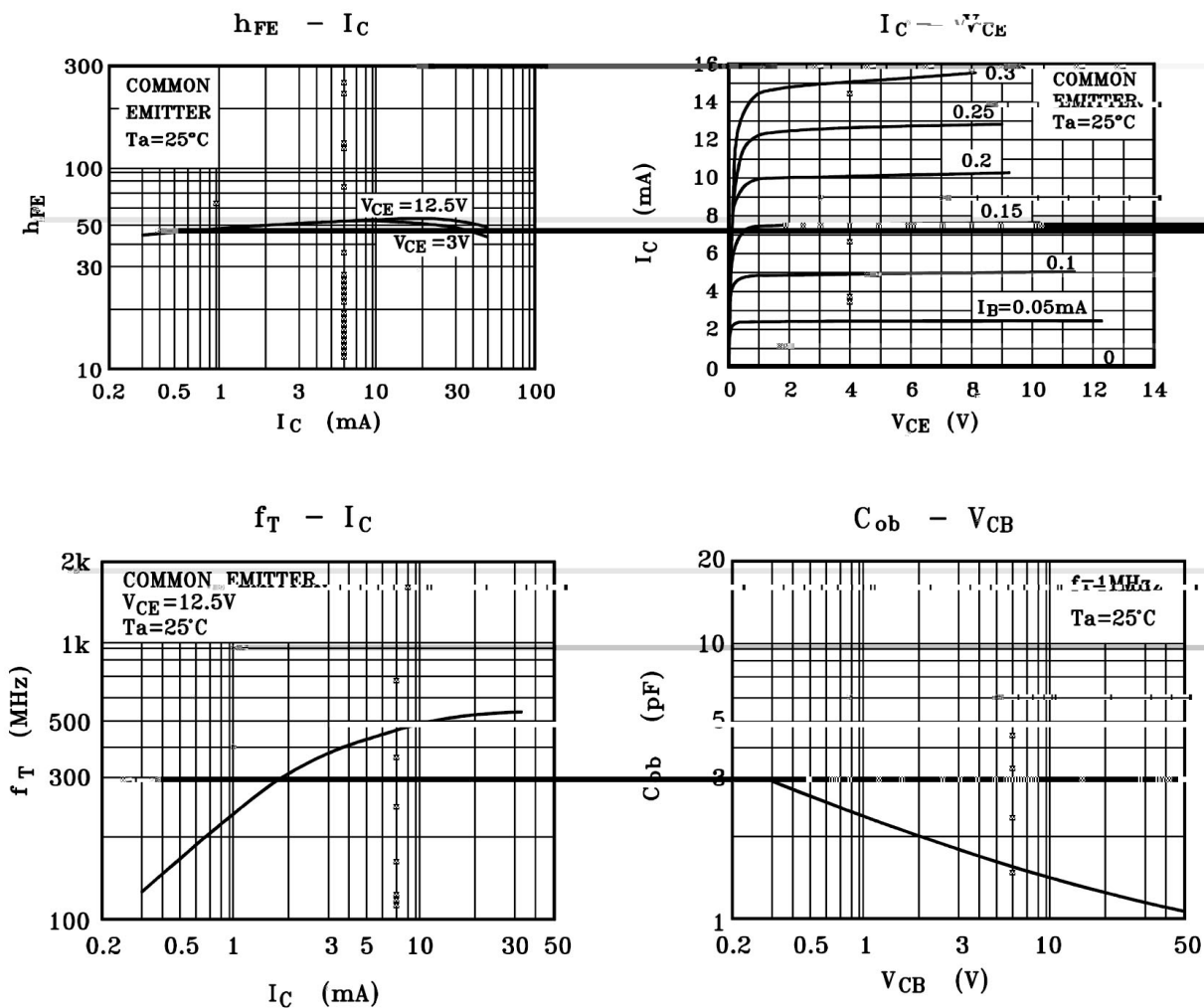
PIN 2 χ Emitter

PIN 3 χ Base

See Marking Instructions.

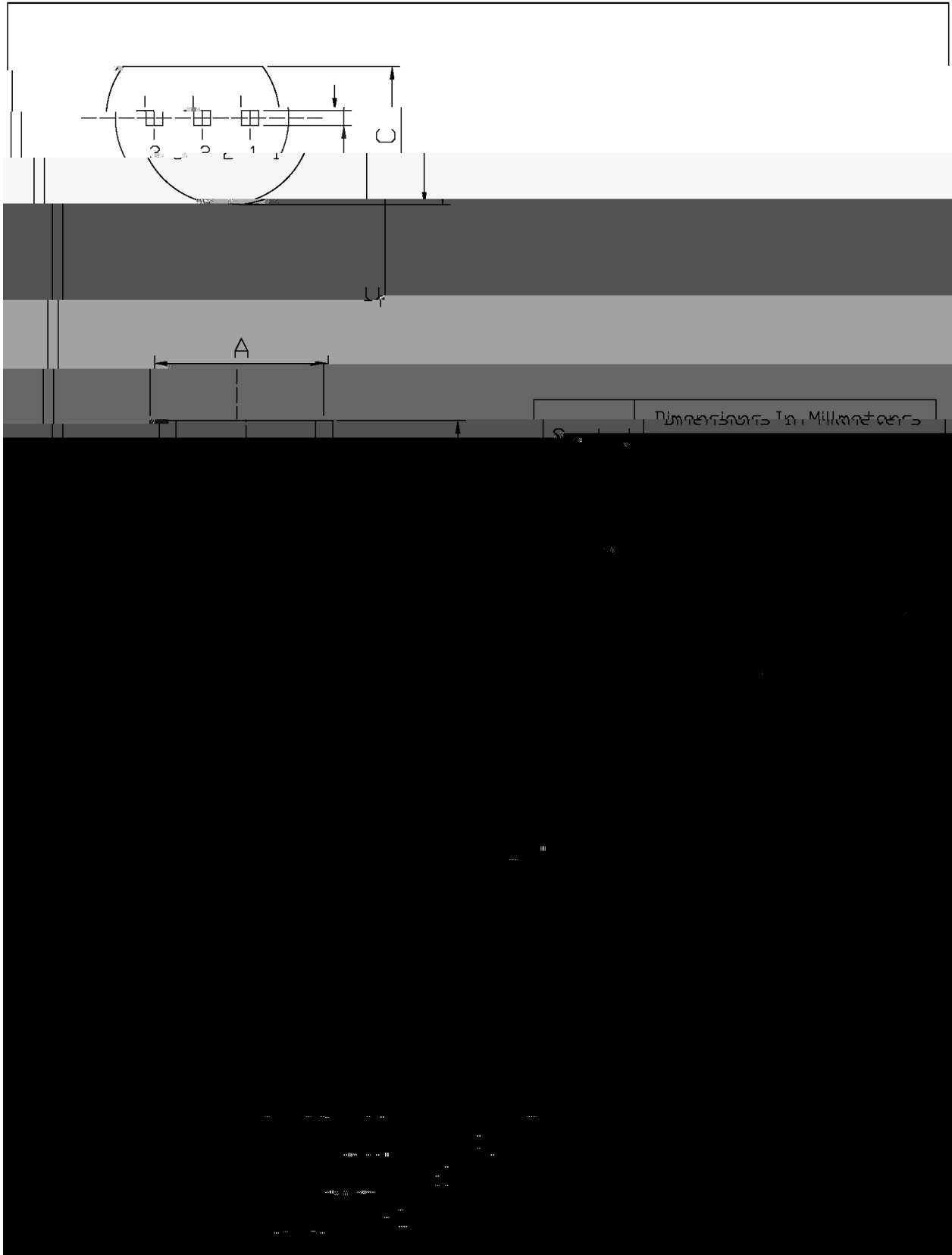
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

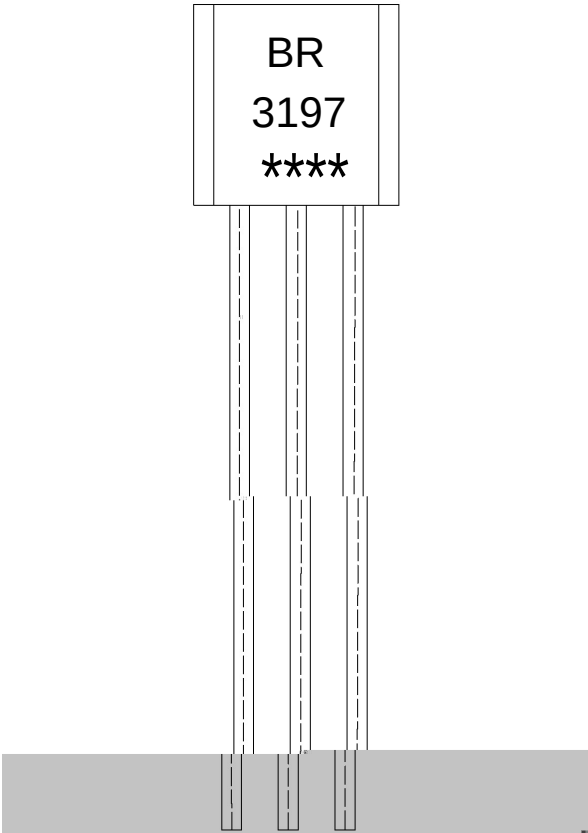
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V



T0-92

Unit: mm





公司代码	公司代码
EU:	产品型号
64<: 芯片	产品型号
---- 芯片	公司代码 产品代码 公司代码 产品代码
Note:	
BR:	Company Code.
3197:	Product Type.
****:	Lot No. Code,code change with Lot No.



说明

1. 预加热: 25~150 °C, 时间: 60~90sec;
2. 峰值温度: 255 °C, 持续时间: 5 °C 0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

- 1.Preheating:25~150 °C , Time:60~90sec.
- 2.Peak Temp.:255 °C , Duration:5 °C 0.5sec.
3. Cooling Speed: 2~10 °C/sec.

温度: 270 °C ± 5 时间: 10 ± 1 sec. Temp: 270 ± 5 Time: 10 ± 1 sec

批量 / BULK